

NPN SILICON POWER DARLINGTON TRANSISTOR 10 AMPERE , 400 VOLTS

CHIP STRUCTURE

- * Dimensions: 188x214 mils²
- * Bond pad size:
 - Emitter: 34x36 mils²
 - Base: 37x 52 mils²
- * Thickness: 11.5~13.5 mils
- * Contact Metallization
 - Front Side: Aluminum
 - Back Side: Silver

CHIPS DIAGRAM



MAXIMUM RATINGS

Characteristic	Symbol	Min	Unit
Collector-Base Voltage	V_{CBO}	600	V
Collector-Emitter Voltage($R_{BE}=27\Omega$)	V_{CER}	550	V
Collector-Emitter Voltage	$V_{CEO(SUS)}$	400	V
Emitter-Base Voltage	V_{EBO}	8	V
Collector Current-Continuous	I_C	10	A
Base Current	I_B	2	A
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ C$ unless otherwise notes)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Sustaining Voltage ($I_C = 200\text{ mA}, I_B = 0, V_{clamp} = \text{Rate } V_{CEO}$)	$V_{CEO(SUS)}$	400		V
Collector-Emitter Sustaining Voltage ($I_C = 200\text{ mA}, I_B = 0, R_{BE}=27\Omega, V_{clamp} = \text{Rate } V_{CER}$)	$V_{CER(SUS)}$	425		V
Collector Cutoff Current (Rate $V_{CER}, R_{BE}=27\Omega$)	I_{CER}		1.0	mA
Collector Cutoff Current (Rate $V_{CBO}, I_E = 0$)	I_{CBO}		1.0	mA
Emitter Cutoff Current ($V_{EB} = 6\text{ V}, I_C = 0$)	I_{EBO}		40	mA
DC Current Gain ($I_C = 3\text{ A}, V_{CE} = 6\text{ V}$) ($I_C = 6\text{ A}, V_{CE} = 6\text{ V}$) ($I_C = 10\text{ A}, V_{CE} = 6\text{ V}$)	h_{FE}	300 100 20	2000	
Collector-Emitter Saturation Voltage ($I_C = 3\text{ A}, I_B = 300\text{ mA}$) ($I_C = 6\text{ A}, I_B = 600\text{ mA}$) ($I_C = 10\text{ A}, I_B = 2\text{ A}$)	$V_{CE(SAT)}$		1.5 2.0 2.5	V
Base-Emitter Saturation Voltage ($I_C = 6\text{ A}, I_B = 600\text{ mA}$) ($I_C = 10\text{ A}, I_B = 2\text{ A}$)	$V_{BE(SAT)}$		2.5 3.0	V
Base-Emitter on Voltage ($I_C = 10\text{ A}, V_{CE} = 6\text{ V}$)	$V_{BE(ON)}$		2.8	V
Diode Forward Voltage ($I_F = 10\text{ A}$)	V_F		3.5	V

Pluse Test: Pluse width = 300uS , Duty Cycle \leq 2.0%

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